

-- This patent resulted from a continuation of U.S. Patent No. 6,333,539, filed on

B¹ October 6, 1998, that is a divisional application of U.S. Patent No. 6,346,439, filed on

July 9, 1996.--

Patent Application Serial No.

08/677,266, New U.S. Pat. No.

In the Preliminary Amendment, filed November 29, 2001, Applicants mistakenly added a duplicative "Related Patent Data" section at p. 1 before the "Technical Field" section. Please delete the entire mistakenly added section, including the heading.

Please replace the abstract with the following clean replacement abstract in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

B² --The invention encompasses a transistor device comprising a region of a semiconductor material, and a transistor gate over a portion of the region. The device comprises a pair of opposing sidewall spacers adjacent sidewalls of the transistor gate and a pair of opposing first conductivity type source/drain regions within the semiconductor material proximate the transistor gate. The entirety of the semiconductor material under one of the sidewall spacers being defined as a first segment, and the entirety of the semiconductor material which is under the other of the sidewall spacers being defined as a second segment. The first and second segments of the semiconductor material are separated from the first and second source/drain regions by first and second gap regions, respectively, of the semiconductor material. The device further comprises a pair of opposing second conductivity type halo regions within the first and second gap regions.--

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